

TECHNICAL DATA  
DATA SHEET 1046, REV. A

**THREE PHASE FULL WAVE  
BRIDGE RECTIFIER ASSEMBLY**

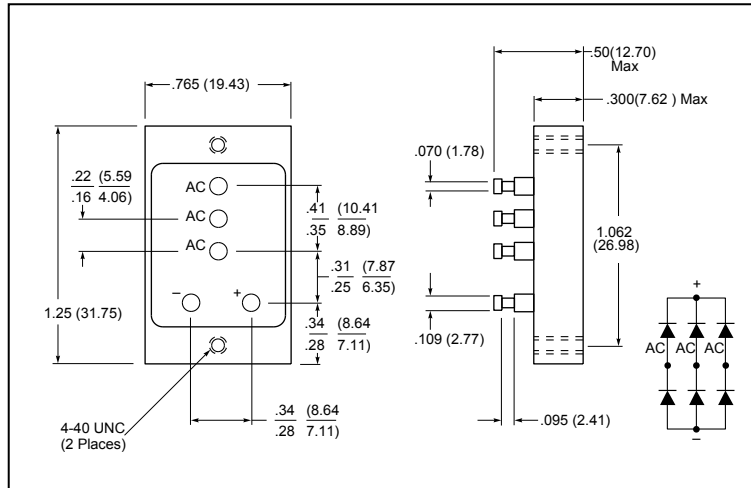
DESCRIPTION: A 200/400/600/800/1000 VOLT, 11 AMP, 5000 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at  $T_A = 25^\circ\text{C}$  unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	-	-	-		Vdc
S10A320				200	
S10A340				400	
S10A360				600	
S10A380				800	
S10A3100				1000	
Average DC Output Current ( $I_o$ ) ( $T_C = \text{Case Temp}$ )	$T_C = 55^\circ\text{C}$ $T_C = 100^\circ\text{C}$ $T_C = 125^\circ\text{C}$	-	-	11 8.0 5.5	Amps
Average DC Output Current Ambient Temp. (no heat sink) ( $I_o$ )	$T_A = 25^\circ\text{C}$ $T_A = 55^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	4.0 3.0 2.0	Amps
Peak Single Cycle Surge Current ( $I_{FSM}$ )	$t_p = 8.3 \text{ ms}$ Single Half Cycle Sine Wave	-	-	100	Amps(pk)
Peak Recurring Surge Current ( $I_{FRM}$ )	$T_A = 25^\circ\text{C}$	-	-	60	Amps
Operating and Storage Temp. ( $T_{op}$ & $T_{stg}$ )	-	-55	-	+150	$^\circ\text{C}$
Maximum Forward Voltage ( $V_f$ )	$I_f = 9.0\text{A}$ (300 $\mu\text{sec}$ pulse, duty cycle < 2%)	-	-	1.3	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	2.0 100	$\mu\text{Amps}$
Reverse Recovery Time ( $t_{rr}$ )	$I_f = 0.5\text{A}$ , $I_r = 1.0\text{A}$ , $I_{rr} = 0.25\text{A}$	-	-	5000	nsec
Thermal Resistance ( $\theta_{JL}$ )	-	-	-	3.0	$^\circ\text{C/W}$

**SENSITRON**  
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**MECHANICAL DIMENSIONS: In Inches / mm**



**FIG. 410**

Notes:  
 Case finish - Black Anodized  
 Potted dimension - uncontrolled

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